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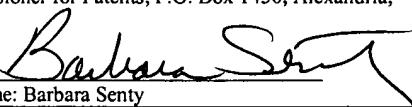
Applicant: Benjamin A. Haskell et al. Examiner: To be assigned
Serial No.: 10/537,385 ✓ Group Art Unit: 2811
Filed: June 3, 2005 Docket: G&C 30794.94-US-WO
Title: GROWTH OF PLANAR, NON-POLAR A-PLANE GALLIUM NITRIDE BY HYDRIDE VAPOR PHASE EPITAXY

CERTIFICATE OF MAILING UNDER 37 CFR 1.10

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We are transmitting herewith the attached:

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By: 
Name: George H. Gates
Reg. No.: 33,500
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By: *Barbara Senty*
Name: Barbara Senty

INFORMATION DISCLOSURE STATEMENT (37 C.F.R. §1.97(b))

MAIL STOP AMENDMENT
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Dear Sir:

With regard to the above-identified application, the items of information listed on the enclosed Form 1449 are brought to the attention of the Examiner.

This statement should be considered because it is submitted before the mailing date of a first Office Action on-the-merits. Accordingly, no fee is due for consideration of the items listed on the enclosed Form 1449.

In accordance with 37 C.F.R. §1.98(a)(2), a copy of each foreign patent document and each non-patent document listed on the enclosed Form 1449 is provided.

No representation is made that a reference is "prior art" within the meaning of 35 U.S.C. §§ 102 and 103 and Applicants reserve the right, pursuant to 37 C.F.R. § 1.131 or otherwise, to establish that

the reference(s) are not "prior art". Moreover, Applicants do not represent that a reference has been thoroughly reviewed or that any relevance of any portion of a reference is intended.

Consideration of the items listed is respectfully requested. Pursuant to the provisions of M.P.E.P. 609, it is requested that the Examiner return a copy of the attached Form 1449, marked as being considered and initialed by the Examiner, to the undersigned with the next official communication.

Please direct any response or inquiry to the below-signed attorney at (310) 641-8797.

Respectfully submitted,

GATES & COOPER LLP
Attorneys for Applicant(s)

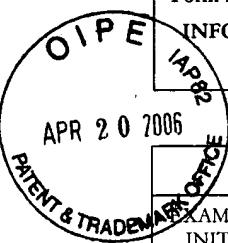
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EXAMINER INITIAL	DOCUMENT NO.	DATE	NAME	CLASS	SUBCLASS
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FOREIGN PATENTS						
	DOCUMENT NO.	DATE	COUNTRY	CLASS	SUBCLASS	TRANSLATION
						YES NO
	WO 2004/061969	07/22/2004	PCT			
	WO 2005/064643	07/14/2005	PCT			
	WO 2004/061909	07/22/2004	PCT			
	0 942 459	09/15/1999	Europe			
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	2002 076329	03/15/2002	Japan (Abstract only)			
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NON-PATENT DOCUMENTS (Including Author, Title, Date, Pertinent Pages, Etc.)

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	32	Leszczynski, M., et. al., "Lattice parameters of gallium nitride" Appl. Phys. Lett. 69 (1), 1 July 1996, pp. 73-75
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	53	Takeuchi, T., et. al., "Determination of piezoelectric fields in strained GaInN quantum wells using the quantum-confined Stark effect" Appl. Phys. Lett. 73 (12), 21 September 1998, pp. 1691-1693
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75	Haskell et al., "Defect reduction in (1120) a-plane gallium nitride via lateral epitaxial overgrowth by hydride vapor-phase epitaxy", <i>Applied Physics Letters</i> , Vol. 83 No. 4 (07/28/03)	
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81	Yue Jun Sun et al., "Nonpolar In _x Ga _{1-x} N/GaN(1100) multiple quantum wells grown on γ -LiAlO ₂ (100) by plasma-assisted molecular-beam epitaxy", <i>Physical Review B</i> 67 (2003)	
82	Takeuchi et al., "Theoretical Study of Orientation Dependence of Piezoelectric Effects in Wurtzite Strained GaInN/GaN Heterostructures and Quantum Wells", <i>Jpn. J. Appl. Phys.</i> Vol. 39, pp. 413-416, Part 1, No. 2A (February 2000)	
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